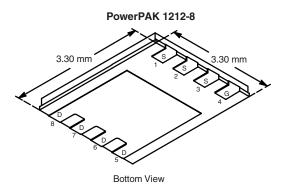


ROHS COMPLIANT

Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
- 12	0.012 at V _{GS} = - 4.5 V	- 15.6			
	0.016 at V _{GS} = - 2.5 V	- 13.5			
	0.024 at V _{GS} = - 1.8 V	- 11			



Si7407DN-T1-E3 (Lead (Pb)-free)

Si7407DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

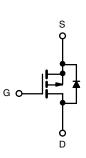
Ordering Information: Si7407DN-T1

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFETS: 1.8 V Rated
 New Low Thermal Resistance PowerPAK[®]
- Package with Low 1.07 mm Profile
- Ultra-Low R_{DS(on)}

APPLICATIONS

- Load Switch
- PA Switch
- Battery Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted Symbol Unit Parameter 10 s **Steady State** Drain-Source Voltage - 12 V_{DS} v Gate-Source Voltage V_{GS} ± 8 T_A = 25 °C - 15.6 - 9.9 Continuous Drain Current (T_J = 150 °C)^a I_D T_A = 85 °C - 11.2 - 7.2 А - 30 **Pulsed Drain Current** I_{DM} - 3.2 - 1.3 Continuous Source Current (Diode Conduction)^a Is T_A = 25 °C 3.8 1.5 P_D w Maximum Power Dissipation^a $T_A = 85 \ ^{\circ}C$ 2.0 0.8 Operating Junction and Storage Temperature Range T_J, T_{stg} - 55 to 150 °C 260 Soldering Recommendations^{b, c}

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum hundling to Anthian Ia	t ≤ 10 s	R _{thJA}	26	33				
Maximum Junction-to-Ambient ^a	Steady State		65	81	°C/W			
Maximum Junction-to-Case	Steady State	R _{thJC}	1.9	2.4				

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

* Pb containing terminations are not RoHS compliant, exemptions may apply

Si7407DN

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -400 \ \mu A$	- 0.40		- 1.0	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -12 V, V_{GS} = 0 V$			- 1	
		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS}{\leq}$ - 5 V, V_{GS} = - 4.5 V	- 30			А
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 15.6 A		0.009	0.012	Ω
		V _{GS} = - 2.5 V, I _D = - 13.5 A		0.013	0.016	
		V _{GS} = - 1.8 V, I _D = - 5 A		0.019	0.024	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 6 V, I _D = - 15.6 A		52		S
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = - 3.2 A, $V_{\rm GS}$ = 0 V		- 0.7	- 1.2	V
Dynamic ^b						
Total Gate Charge	Qg			39	59	nC
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 V, V_{GS} = -4.5 V, I_{D} = -15.6 A$		6		
Gate-Drain Charge	Q _{gd}			11		
Turn-On Delay Time	t _{d(on)}			30	45	
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		50	75	ns
Turn-Off DelayTime	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		200	300	
Fall Time	t _f			165	250	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 3.2 A, di/dt = 100 A/μs		60	90	

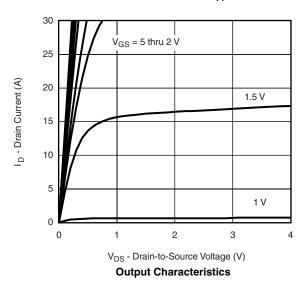
Notes:

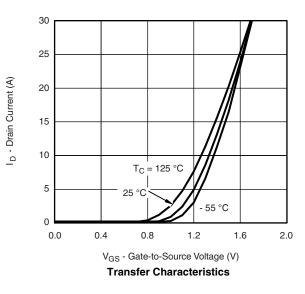
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

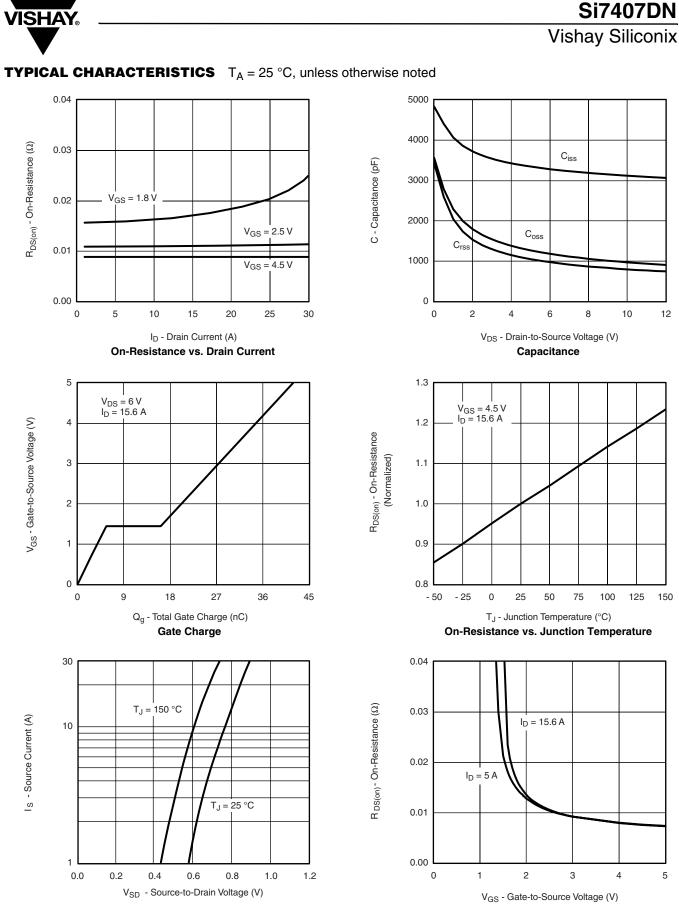
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $T_A = 25 \text{ °C}$, unless otherwise noted



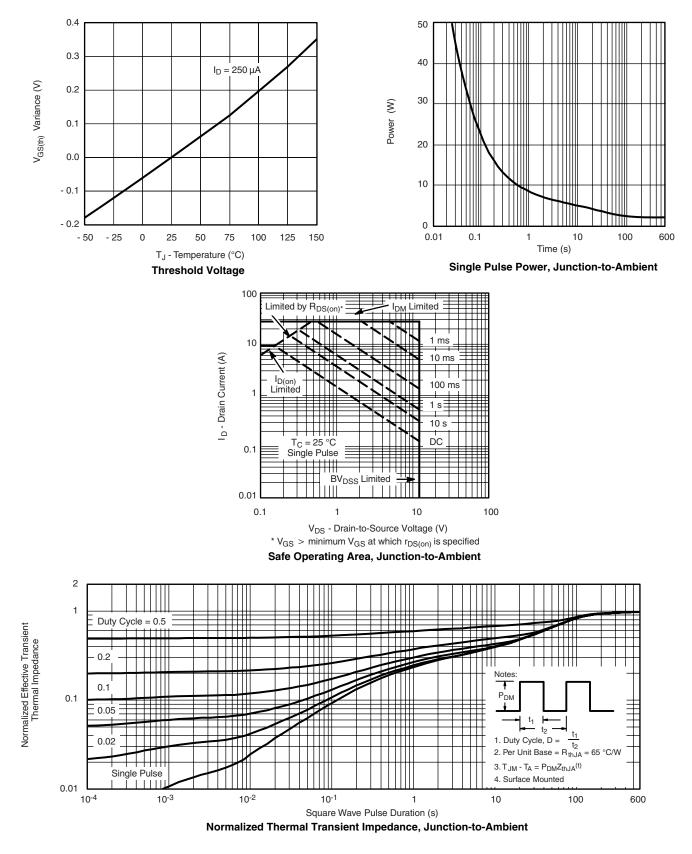




Document Number: 71912 S-80581-Rev. D, 17-Mar-08 On-Resistance vs. Gate-to-Source Voltage

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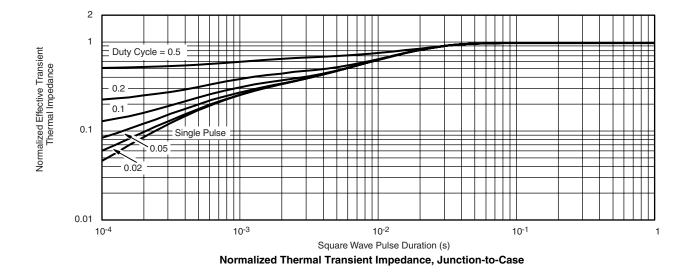
TYPICAL CHARACTERISTICS $T_A = 25 \text{ °C}$, unless otherwise noted





Si7407DN Vishay Siliconix

TYPICAL CHARACTERISTICS $T_A = 25 \text{ °C}$, unless otherwise noted



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